

FEATURES

- Double Side Cooling
- High Reliability In Service
- High Voltage Capability
- Fault Protection Without Fuses
- High Surge Current Capability
- Turn-off Capability Allows Reduction In Equipment Size And Weight. Low Noise Emission Reduces Acoustic Cladding Necessary For Environmental Requirements

APPLICATIONS

- Variable speed A.C. motor drive inverters (VSD-AC).
- Uninterruptable Power Supplies
- High Voltage Converters.
- Choppers.
- Welding.
- Induction Heating.
- DC/DC Converters.

KEY PARAMETERS

I_{TCM}	3000A
V_{DRM}	4500V
$I_{T(AV)}$	1100A
dV_D/dt	750V/μs
dI_T/dt	300A/μs

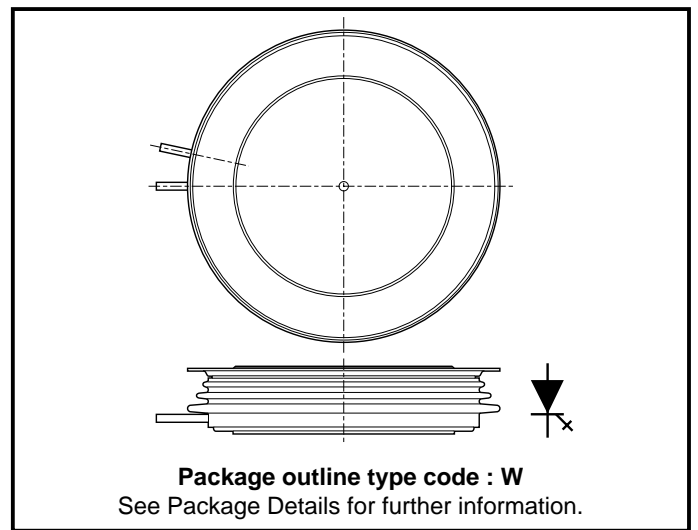


Fig.1 Package outline

VOLTAGE RATINGS

Type Number	Repetitive Peak Off-state Voltage V_{DRM} V	Repetitive Peak Reverse Voltage V_{RRM} V	Conditions
DG858DW45	4500	16	$T_{vj} = 125^{\circ}C, I_{DRM} = 100mA, I_{RRM} = 50mA$

CURRENT RATINGS

Symbol	Parameter	Conditions	Max.	Units
I_{TCM}	Repetitive peak controllable on-state current	$V_D = V_{DRM}, T_i = 125^{\circ}C, di_{GQ}/dt = 40A/\mu s, C_s = 4.0\mu F, L_s \leq 200nH$	3000	A
$I_{T(AV)}$	Mean on-state current	$T_{HS} = 80^{\circ}C$. Double side cooled, half sine 50Hz.	1100	A
$I_{T(RMS)}$	RMS on-state current	$T_{HS} = 80^{\circ}C$. Double side cooled, half sine 50Hz.	1720	A

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SURGE RATINGS

Symbol	Parameter	Conditions	Max.	Units
I_{TSM}	Surge (non-repetitive) on-state current	10ms half sine. $T_j = 125^\circ\text{C}$	20.0	kA
I^2t	I^2t for fusing	10ms half sine. $T_j = 125^\circ\text{C}$	2.0×10^6	A^2s
di_T/dt	Critical rate of rise of on-state current	$V_D = 3000\text{V}$, $I_T = 3000\text{A}$, $T_j = 125^\circ\text{C}$ $I_{FG} > 40\text{A}$, Rise time $< 1.0\mu\text{s}$	300	$\text{A}/\mu\text{s}$
dV_D/dt	Rate of rise of off-state voltage	To 66% V_{DRM} ; $R_{GK} \leq 22\Omega$, $T_j = 125^\circ\text{C}$	20	$\text{V}/\mu\text{s}$
		To 66% V_{DRM} ; $V_{RG} = -2\text{V}$, $T_j = 125^\circ\text{C}$	750	$\text{V}/\mu\text{s}$
L_S	Peak stray inductance in snubber circuit	$I_T = 3000\text{A}$, $V_D = V_{DRM}$, $T_j = 125^\circ\text{C}$, $di_{GQ}/dt = 40\text{A}/\mu\text{s}$, $C_s = 4.0\mu\text{F}$	200	nH

GATE RATINGS

Symbol	Parameter	Conditions	Min.	Max.	Units
V_{RGM}	Peak reverse gate voltage	This value maybe exceeded during turn-off	-	16	V
I_{FGM}	Peak forward gate current		20	100	A
$P_{FG(AV)}$	Average forward gate power		-	20	W
P_{RGM}	Peak reverse gate power		-	24	kW
di_{GQ}/dt	Rate of rise of reverse gate current		20	60	$\text{A}/\mu\text{s}$
$t_{ON(min)}$	Minimum permissible on time		50	-	μs
$t_{OFF(min)}$	Minimum permissible off time		100	-	μs

THERMAL AND MECHANICAL DATA

Symbol	Parameter	Conditions	Min.	Max.	Units
$R_{th(j-hs)}$	DC thermal resistance - junction to heatsink surface	Double side cooled	-	0.011	$^\circ\text{C}/\text{W}$
		Anode side cooled	-	0.017	$^\circ\text{C}/\text{W}$
		Cathode side cooled	-	0.03	$^\circ\text{C}/\text{W}$
$R_{th(c-hs)}$	Contact thermal resistance	Clamping force 40kN With mounting compound	-	0.0021	$^\circ\text{C}/\text{W}$
T_{vj}	Virtual junction temperature		-40	125	$^\circ\text{C}$
T_{OP}/T_{stg}	Operating junction/storage temperature range		-40	125	$^\circ\text{C}$
-	Clamping force		36.0	44.0	kN

CHARACTERISTICS

T_j = 125°C unless stated otherwise					
Symbol	Parameter	Conditions	Min.	Max.	Units
V _{TM}	On-state voltage	At 3000A peak, I _{G(ON)} = 10A d.c.	-	3.85	V
I _{DM}	Peak off-state current	V _{DRM} = 4500V, V _{RG} = 2V	-	100	mA
I _{RRM}	Peak reverse current	At V _{RRM}	-	50	mA
V _{GT}	Gate trigger voltage	V _D = 24V, I _T = 100A, T _j = 25°C	-	1.2	V
I _{GT}	Gate trigger current	V _D = 24V, I _T = 100A, T _j = 25°C	-	4.0	A
I _{RGM}	Reverse gate cathode current	V _{RGM} = 16V, No gate/cathode resistor	-	50	mA
E _{ON}	Turn-on energy	V _D = 2000V	-	4400	mJ
t _d	Delay time	I _T = 3000A, di _T /dt = 300A/μs	-	2.0	μs
t _r	Rise time	I _{FG} = 40A, rise time < 1.0μs	-	6.0	μs
E _{OFF}	Turn-off energy	I _T = 3000A, V _{DM} = 4200V Snubber Cap Cs = 4.0μF, di _{GQ} /dt = 40/μs	-	12500	mJ
t _{gs}	Storage time		-	26	μs
t _{gf}	Fall time		-	2.5	μs
t _{gq}	Gate controlled turn-off time		-	28.5	μs
Q _{GQ}	Turn-off gate charge		-	12500	μC
Q _{GQT}	Total turn-off gate charge		-	25000	μC
I _{GQM}	Peak reverse gate current		-	950	A

RELIABILITY

	Conditions	Limit	Units
DC blocking reliability	V _{dc} = 3500V, T _j = -40 to + 125°C, ambient cosmic radiation at sea level, in open air, 100% duty cycle.	100	FIT

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CURVES

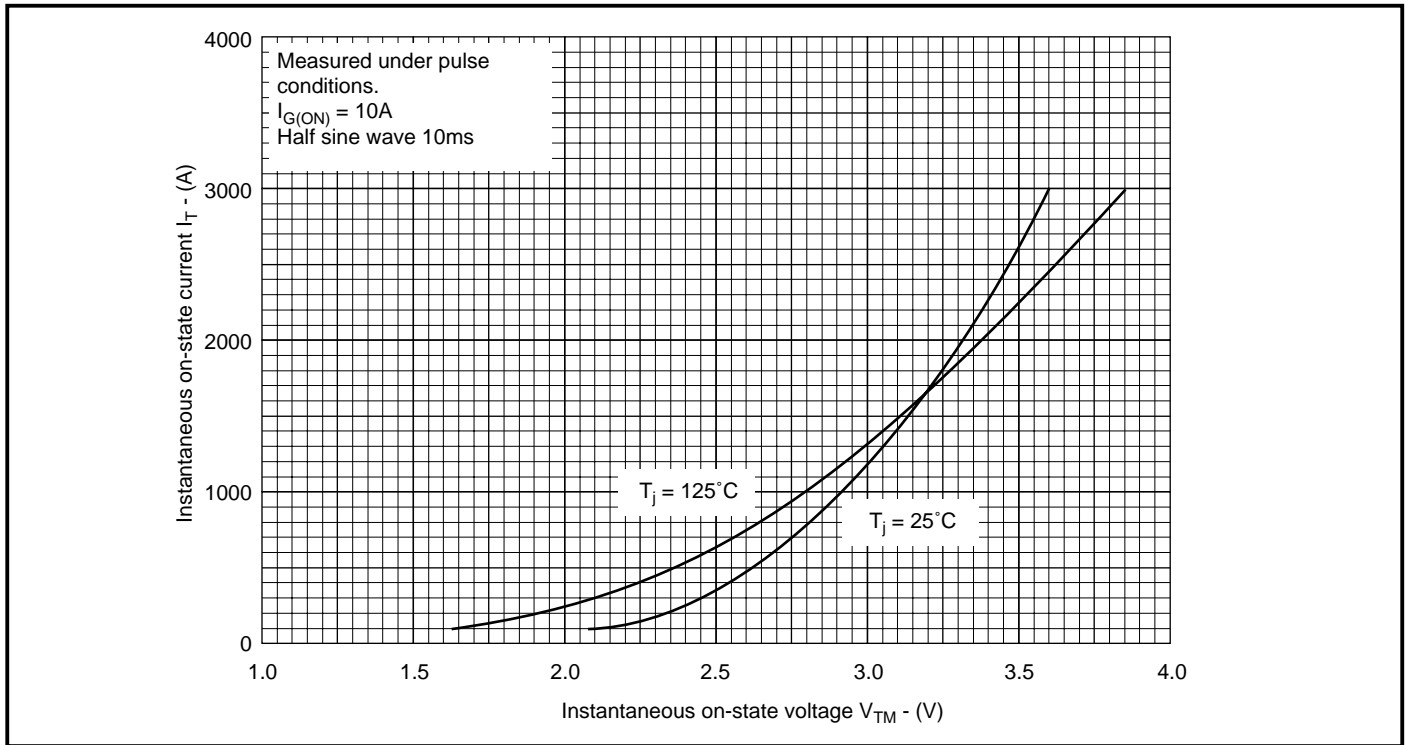
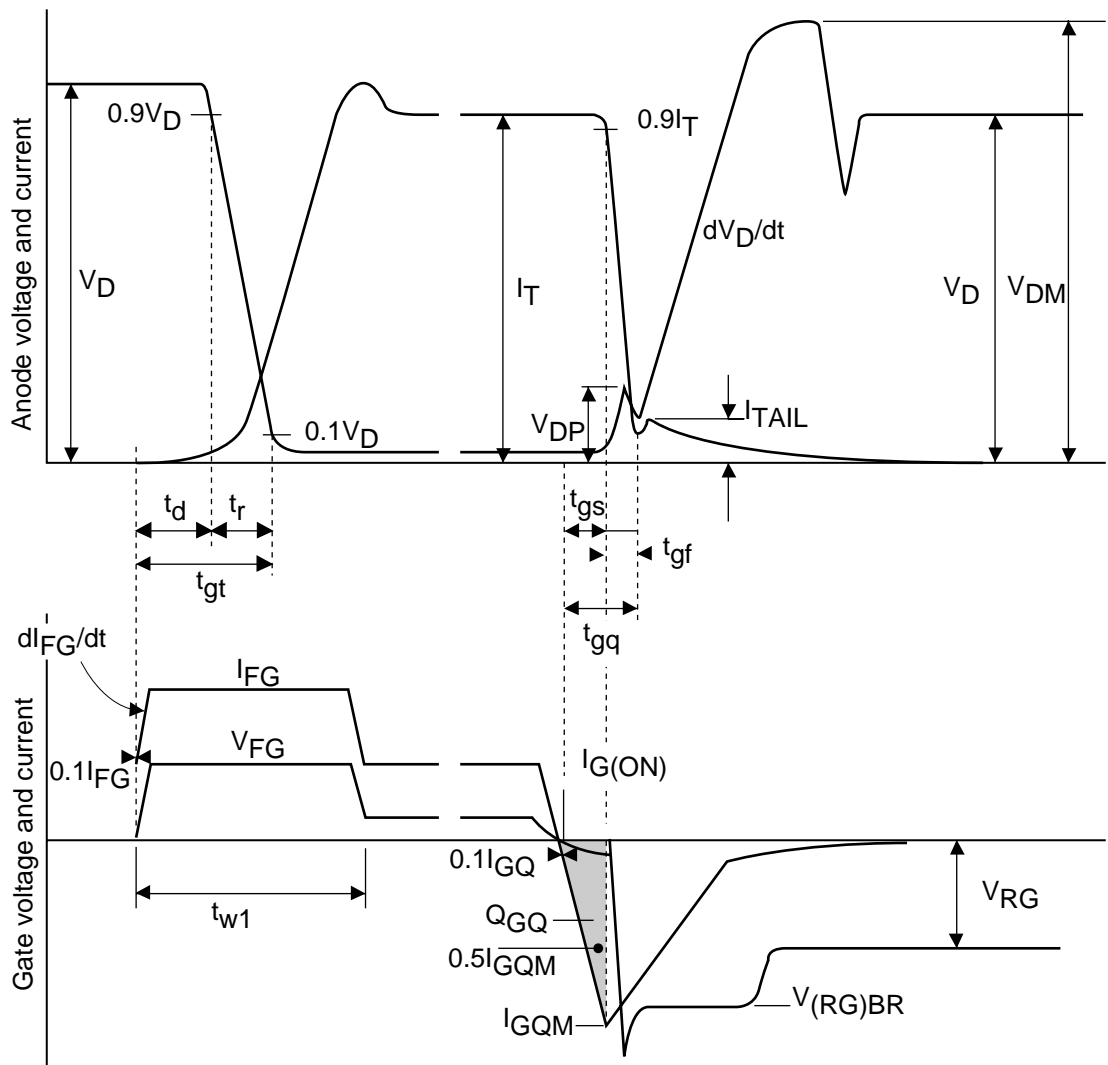


Figure 2. On-state characteristics



Recommended gate conditions:

- $I_{TCM} = 3000A$
- $I_{FG} = 40A$
- $I_{G(ON)} = 10A$ d.c.
- $t_{w1(min)} = 20\mu s$
- $I_{GQM} = 1200A$
- $di_{GQ}/dt = 40A/\mu s$
- $Q_{GQ} = 12500\mu C$
- $V_{RG(min)} = 2V$
- $V_{RG(max)} = 18V$

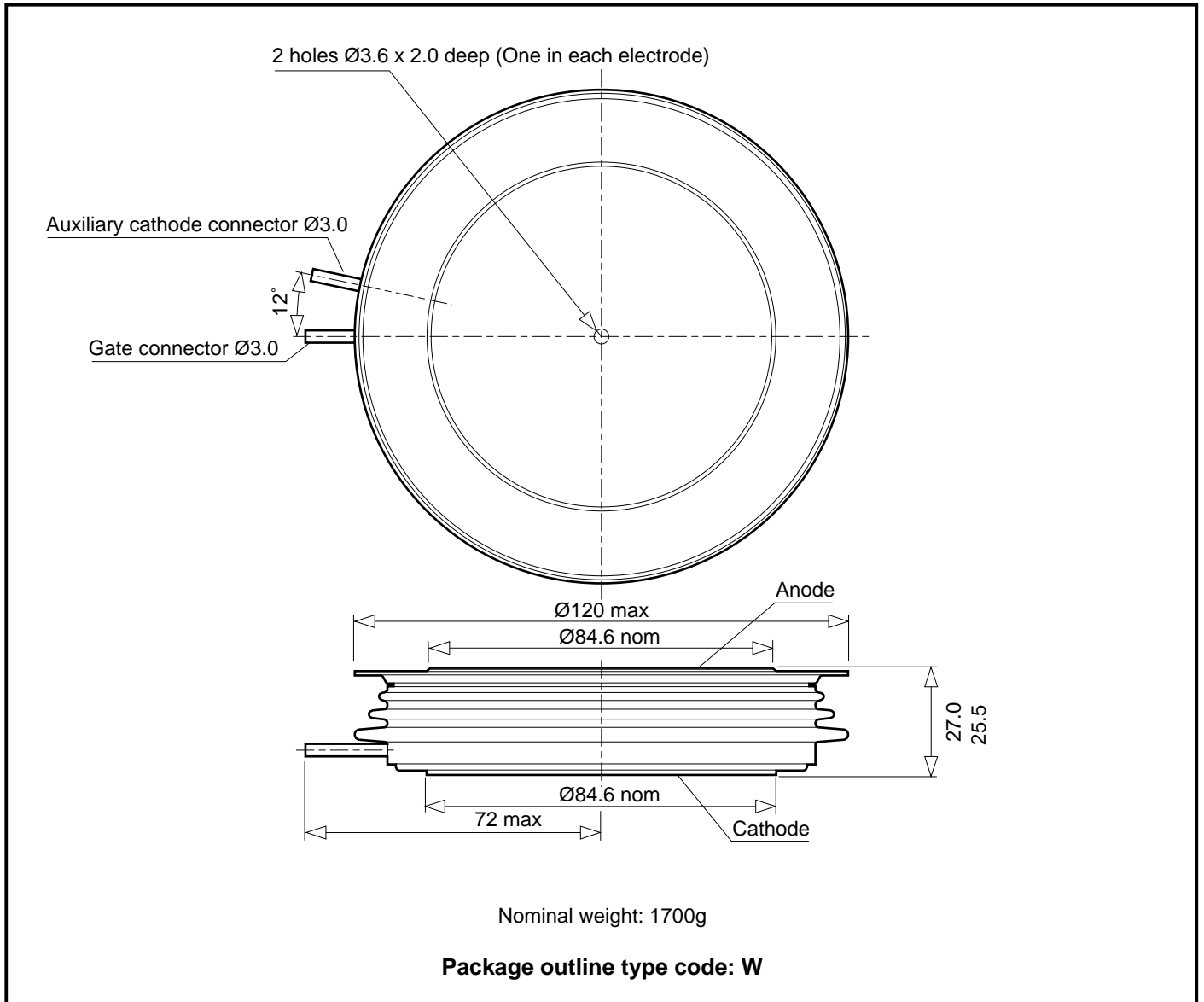
These are recommended Dynex Semiconductor conditions. Other conditions are permitted according to users gate drive specifications.

Figure 3. General switching waveforms

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PACKAGE DETAILS

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.



POWER ASSEMBLY CAPABILITY

The Power Assembly group was set up to provide a support service for those customers requiring more than the basic semiconductor, and has developed a flexible range of heatsink and clamping systems in line with advances in device voltages and current capability of our semiconductors.

We offer an extensive range of air and liquid cooled assemblies covering the full range of circuit designs in general use today. The Assembly group offers high quality engineering support dedicated to designing new units to satisfy the growing needs of our customers.

Using the latest CAD methods our team of design and applications engineers aim to provide the Power Assembly Complete Solution (PACs).

HEATSINKS

The Power Assembly group has its own proprietary range of extruded aluminium heatsinks which have been designed to optimise the performance of Dynex semiconductors. Data with respect to air natural, forced air and liquid cooling (with flow rates) is available on request.

For further information on device clamps, heatsinks and assemblies, please contact your nearest sales representative or Customer Services.

Stresses above those listed in this data sheet may cause permanent damage to the device. In extreme conditions, as with all semiconductors, this may include potentially hazardous rupture of the package. Appropriate safety precautions should always be followed.



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